Listing of Claims:

- 1. (Currently Amended) Method A method for depositing a material (3) on a substrate wafer (1) having the following method steps:
 - (a) <u>providing provision of</u> the substrate wafer (1), which has a growth area (4) intended for a later material deposition[[,]];
 - (b) <u>applying application of a thermal radiation absorption layer (2), which</u> exhibits a good absorption of thermal radiation, on the <u>a</u> rear side (5) of the substrate wafer (1) [[,]] which faces away from the growth area (4)[[,]];
 - (c) heating of the substrate wafer (1) to the \underline{a} deposition temperature [[,]];
 - (d) <u>depositing deposition of a material (3) onto the growth area (4) of the substrate wafer (1) by an MOVPE method;</u>

wherein the thermal radiation absorption layer is applied before deposition of the material onto the growth area of the substrate wafer.

- 2. (Currently Amended) Method The method according to Claim 1, in which the deposited material (3) to be deposited is a semiconductor material.
- 3. (Currently Amended) Method The method according to Claim 1, in which the deposited material (3) to be deposited comprises at least one layer made of $Al_xGa_yIn_{1-x-y}N$, where $0 \le x+y \le 1$, $0 \le x \le 1$, $0 \le y \le 1$ apply.
- 4. (Currently Amended) Method The method according to claim 1, in which a substrate wafer is used which essentially comprises SiC or an SiC-based material.

- 5. (Currently Amended) Method The method according to claim 1, in which a material or a material mixture which exhibits inert behaviour during the deposition method in accordance with method step (d) is applied as the thermal radiation absorption layer (2).
- 6. (Currently Amended) Method The method according to claim 1, in which a material or a material mixture which is compatible with <u>a</u> the material and/or <u>a</u> the contact-connecting process of an electrical contact that is to be applied later, is applied as the thermal radiation absorption layer (2).
- 7. (Currently Amended) Method The method according to claim 1, in which the thermal radiation absorption layer (2) is applied by means of sputtering in accordance with method step (b).
- 8. (Currently Amended) Method The method according to claim 1, in which a doped Si layer, in particular a highly doped Si layer, is used as the thermal radiation absorption layer (2).
- 9. (Currently Amended) Method The method according to Claim 8, in which the Si layer is applied with a thickness which lies between 10 nm and 20 μm inclusive.
- 10. (Currently Amended) Method The method according to Claim 8, in which the Si layer has a doping of at least 1×10^{19} /cm³.

- 11. (Currently Amended) Method The method according to claim 1, in which the heating in accordance with method step (c) is essentially effected by means of thermal radiation.
- 12. (Currently Amended) Method The method according to claim 1, in which, in method step (c), a heating source is used which generates thermal radiation of a spectral range for which the thermal radiation absorption layer (2) exhibits good radiation absorption.